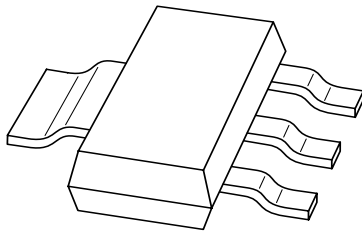


# DATA SHEET



## **BAT120 series** Schottky barrier double diodes

Product data sheet  
Supersedes data of 2001 Aug 27

2003 Aug 04

Schottky barrier double diodes

BAT120 series

FEATURES

- Low switching losses
- Capability of absorbing very high surge current
- Fast recovery time
- Guard ring protected
- Plastic SMD package.

APPLICATIONS

- Low power switched-mode power supplies
- Rectification
- Polarity protection.

DESCRIPTION

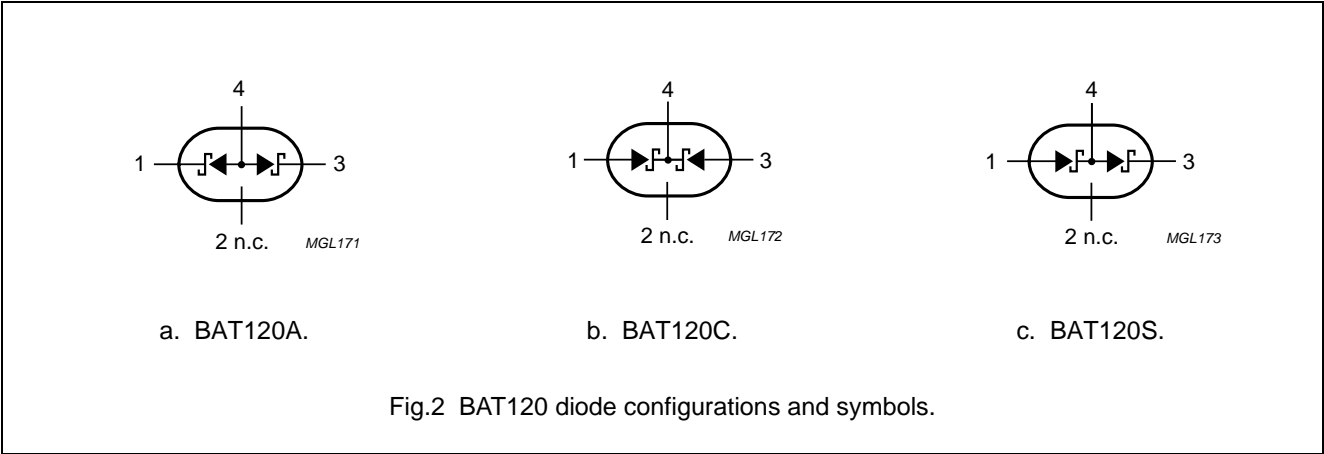
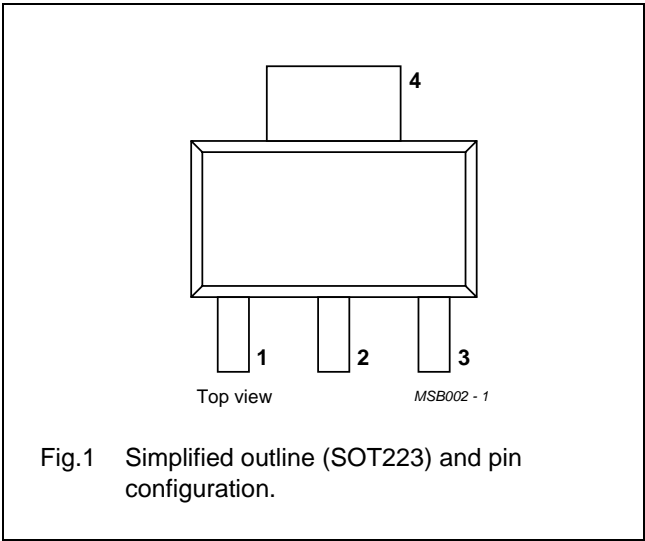
Planar Schottky barrier double diodes encapsulated in a SOT223 plastic SMD package.

MARKING

TYPE NUMBER	MARKING CODE
BAT120A	AT120A
BAT120C	AT120C
BAT120S	AT120S

PINNING

PIN	BAT120		
	A	C	S
1	k <sub>1</sub>	a <sub>1</sub>	a <sub>1</sub>
2	n.c.	n.c.	n.c.
3	k <sub>2</sub>	a <sub>2</sub>	k <sub>2</sub>
4	a <sub>1</sub> , a <sub>2</sub>	k <sub>1</sub> , k <sub>2</sub>	k <sub>1</sub> , a <sub>2</sub>



## Schottky barrier double diodes

## BAT120 series

## LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
<b>Per diode</b>					
$V_R$	continuous reverse voltage		–	25	V
$I_F$	continuous forward current		–	1	A
$I_{FSM}$	non-repetitive peak forward current	$t_p < 10$ ms; half sinewave; JEDEC method	–	10	A
$I_{RSM}$	non-repetitive peak reverse current	$t_p = 100$ $\mu$ s	–	0.5	A
$T_{stg}$	storage temperature		–65	+150	°C
$T_j$	junction temperature		–	125	°C
$T_{amb}$	operating ambient temperature		–65	+125	°C

## ELECTRICAL CHARACTERISTICS

$T_{amb} = 25$  °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
<b>Per diode</b>					
$V_F$	forward voltage	see Fig.3 $I_F = 100$ mA $I_F = 1$ A	260 400	300 450	mV mV
$I_R$	reverse current	$V_R = 20$ V; note 1; see Fig.4	80	500	$\mu$ A
		$V_R = 25$ V; note 1; see Fig.4	–	1	mA
		$V_R = 20$ V; $T_j = 100$ °C; note 1	–	10	mA
$C_d$	diode capacitance	$f = 1$ MHz; $V_R = 4$ V; see Fig.5	100	–	pF

## Note

1. Pulse test:  $t_p = 300$   $\mu$ s;  $\delta = 0.02$ .

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	100	K/W

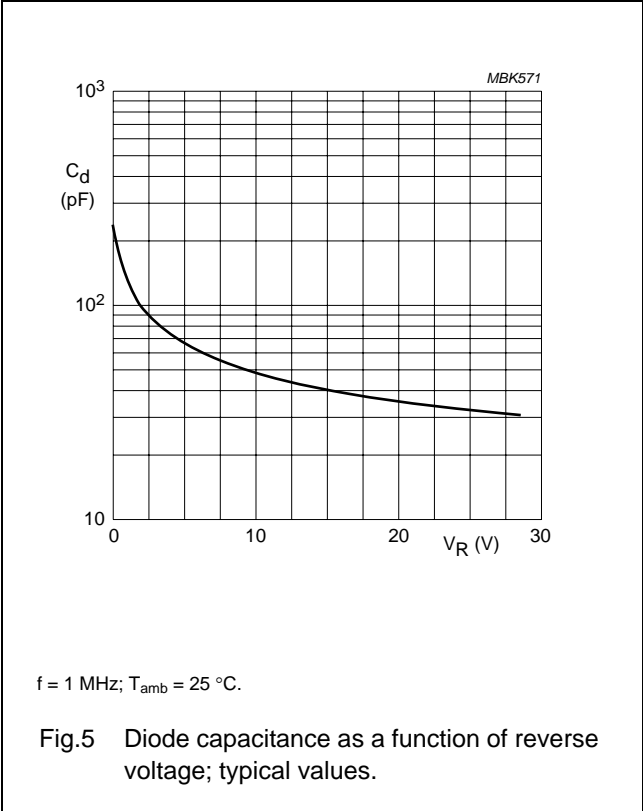
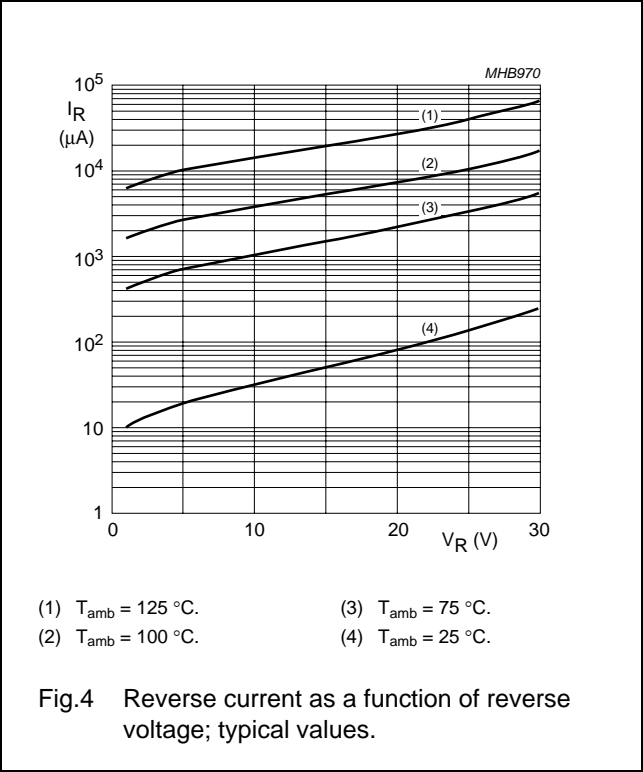
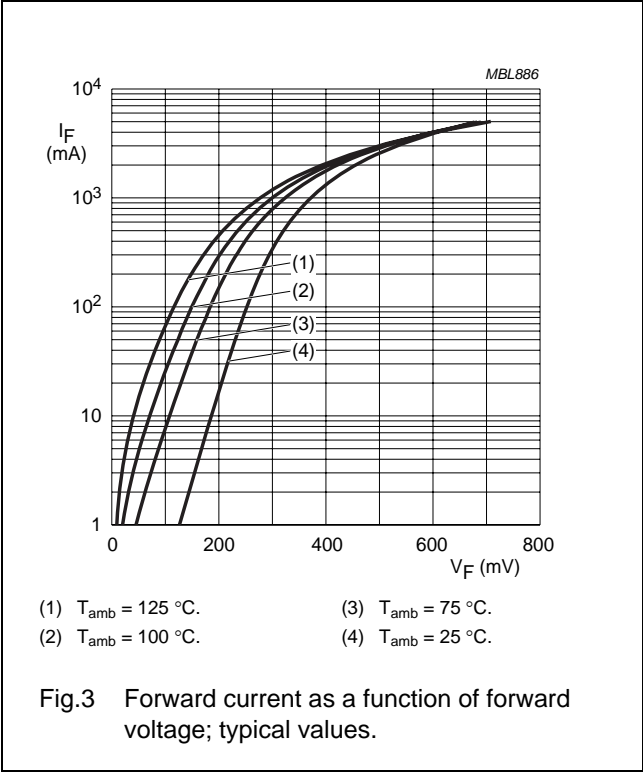
## Note

1. Refer to SOT223 standard mounting conditions.

Schottky barrier double diodes

BAT120 series

GRAPHICAL DATA



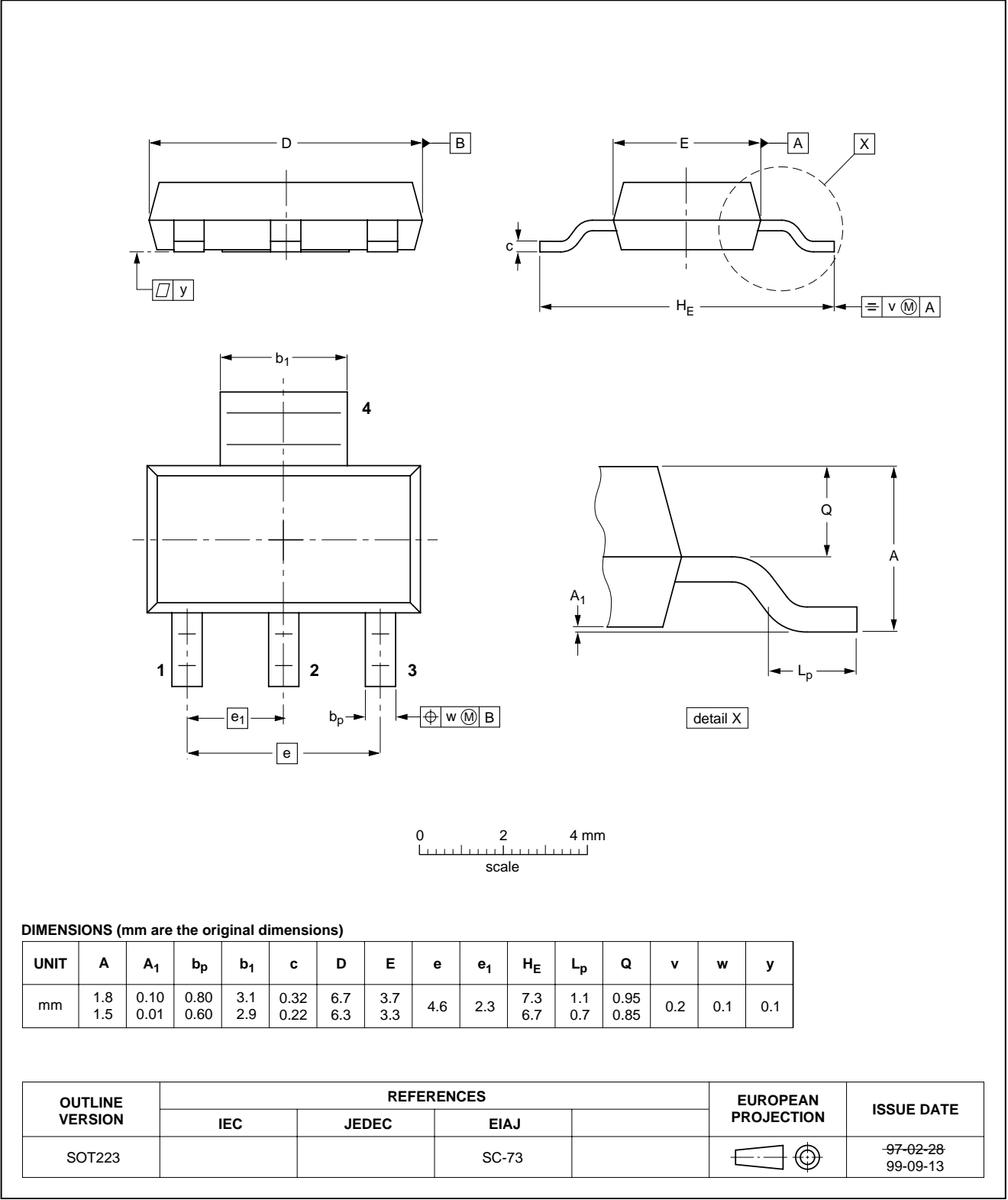
Schottky barrier double diodes

BAT120 series

PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 4 leads

SOT223



## Schottky barrier double diodes

## BAT120 series

## DATA SHEET STATUS

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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Printed in The Netherlands

613514/04/pp7

Date of release: 2003 Aug 04

Document order number: 9397 750 11054

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